

LOW VOLTAGE ANTIFUSE DEVICE AND PROCESS

ABSTRACT OF THE DISCLOSURE

5

A method of producing an antifuse includes introducing nitrogen by ion implantation means into the substrate. An oxide dielectric layer is then formed on the nitrided substrate in a wet oxidation ambient. The conditions of the ion implantation and the oxidation are controlled to generate a dielectric with uniform thickness and a

10 low breakdown voltage when subjected to a high electric field.